Abstracts

Large-Signal Relaxation-Time Model for HEMTs and MESFETs

M.C. Foisy, P.E. Jeroma and G.H. Martin. "Large-Signal Relaxation-Time Model for HEMTs and MESFETs." 1992 MTT-S International Microwave Symposium Digest 92.1 (1992 Vol. I [MWSYM]): 251-254.

A nonquasi-static charge-conserving spline-based model has been implemented in the EEsof harmonic-balance simulator. The model uses a relaxation-time approximation to deseribe the intrinsic charging dynamics of unipolar transistors under arbitrary excitation. On-wafer large-signal measurements of HEMTs closely match simulation results.

❑ Return to main document.